

## Description

The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector in a plastic DIP6 package with different lead forming options.

## Features

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range - 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- UL-approved: UL1577, File No.E492440

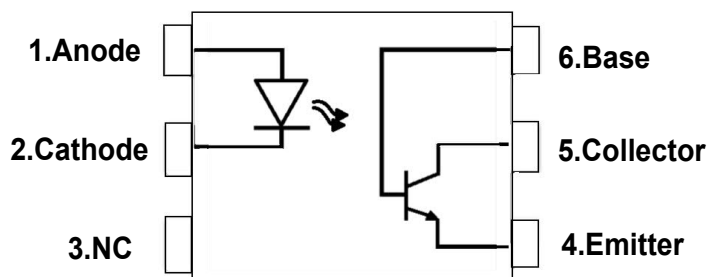
Truth Table (Positive Logic)

Input	Enable	Output
H	H	L
L	H	H
H	L	H
L	L	H
H	NC	L
L	NC	H

## Applications

- Sequence controller
- Telephone/FAX
- System appliances, measuring instrument
- Programmable logic controller

## Schematics



**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT	NOTE
<b>INPUT</b>				
Forward Current	$I_F$	50	mA	
Peak Forward Current( $t=10\mu s$ )	$I_{FM}$	1	A	1
Reverse Voltage	$V_R$	6	V	
Power Dissipation( $T_A=25^\circ C$ )	$P_D$	70	mW	
<b>OUTPUT</b>				
Collector - Emitter Voltage	$V_{CEO}$	80	V	
Collector-Base Breakdown Voltage	$V_{CBO}$	80	V	
Emitter - Collector Voltage	$V_{ECO}$	7	V	
Emitter-Base Breakdown Voltage	$V_{EBO}$	7	V	
Collector Current	$I_C$	80	mA	
Power Dissipation( $T_A=25^\circ C$ )	$P_C$	150	mW	
<b>COMMON</b>				
Total Power Dissipation	$P_{tot}$	200	mW	
Isolation Voltage	$V_{iso}$	5000	V <sub>rms</sub>	2
Operating Temperature	$T_{opr}$	-55~+110	°C	
Storage Temperature	$T_{stg}$	-55~+110	°C	
Soldering Temperature	$T_{sol}$	260	°C	

Note 1. AC For 1 Minute, R.H. = 40 ~ 60%

Note 2. For 10 seconds

**ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C**

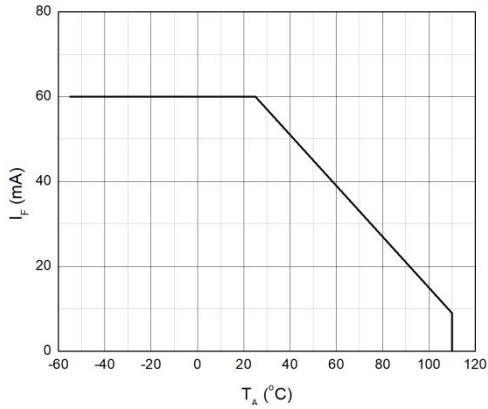
PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE
<b>INPUT</b>							
Forward Voltage	$V_F$	-	1.24	1.4	V	$I_F=10\text{mA}$	
Reverse Current	$I_R$	-	-	10	$\mu\text{A}$	$V_R=6\text{V}$	
Input Capacitance	$C_{in}$	-	30	-	pF	$V=0, f=1\text{kHz}$	
<b>OUTPUT</b>							
Collector Dark Current	$I_{CEO}$	-	-	20	nA	$V_{CE}=10\text{V}, I_F=0$	
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	80	-	-	V	$I_C=1\text{mA}, I_F=0$	
Emitter-Collector Breakdown Voltage	$BV_{ECO}$	7	-	-	V	$I_E=1\text{mA}, I_F=0$	
Collector-Base Breakdown	$BV_{CBO}$	80	-	-	V	$I_C=0.1\text{mA}, I_F=0$	
Emitter-Base Breakdown	$BV_{EBO}$	7	-	-	V	$I_E=0.1\text{mA}, I_F=0$	

**TRANSFER CHARACTERISTICS**

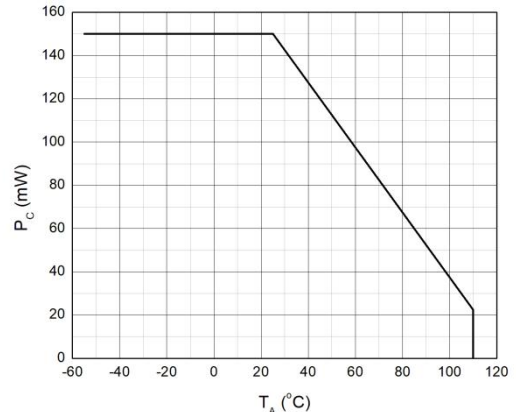
Current Transfer Ratio	CTR	4N35, 4N36, 4N37	100	-	-	%	IF=10mA, VCE=10V
		4N25,4N26, 4N38	20	-	-		
		4N27, 4N28	10	-	-		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	4N25,4N26, 4N27,4N28	-	-	0.5	V	IF=10mA, VCE=10V
		4N35,4N36,4N37	-	-	0.3		IF= 10mA, IC= 0.5mA
		4N38	-	-	1.0		IF= 20mA, IC= 4mA
		4N25,4N26, 4N27,4N28	-	-	0.5		IF= 50mA, IC= 2mA
Isolation Resistance		R <sub>IO</sub>	10 <sup>12</sup>	10 <sup>14</sup>	-	Ω	V <sub>IO</sub> =500Vdc.
Floating Capacitance		C <sub>IO</sub>	-	0.2	1	pF	V=0, f=1MHz
Cut-off Frequency		f <sub>c</sub>	-	6	-	kHz	VCE=5V, IC=2mA RL=100Ω,-3dB
Turn On Time	t <sub>on</sub>	4N25,4N26,4N27, 4N28	-	3	15	-	IF= 10mA, VCC= 10V, RL= 100Ω
		4N35,4N36,4N37, 4N38	-	10	12	-	Ic= 2mA, VCC= 10V, RL= 100Ω
Turn Off Time	t <sub>off</sub>	4N25,4N26,4N27, 4N28	-	3	16	-	IF= 10mA, VCC= 10V, RL= 100Ω
		4N35,4N36,4N37, 4N38	-	9	12	-	Ic= 10mA, VCC= 10V, RL= 100Ω

## CHARACTERISTIC CURVES

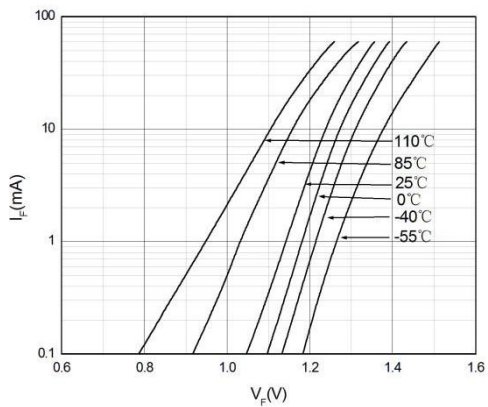
**Fig.1 Forward Current vs. Ambient Temperature**



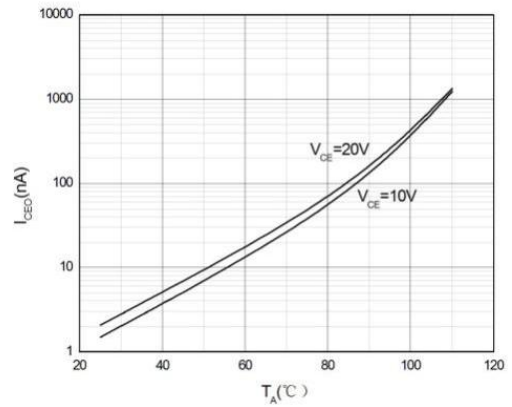
**Fig.2 Collector Power Dissipation vs. Ambient Temperature**



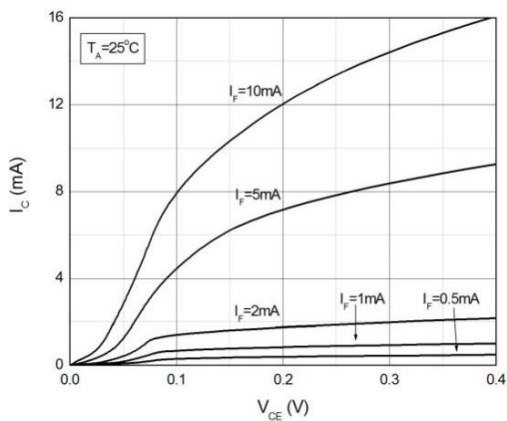
**Fig.3 Forward Current vs. Forward Voltage**



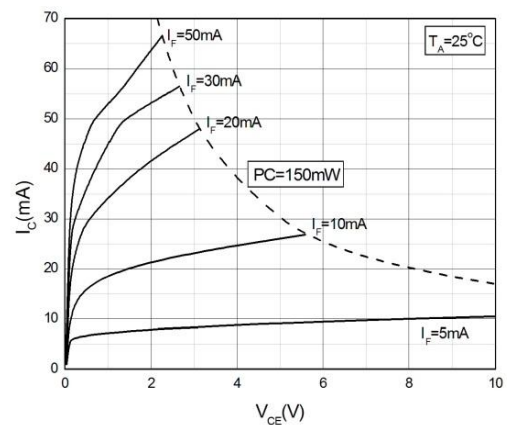
**Fig.4 Collector Dark Current vs. Ambient Temperature**



**Fig.5 Collector Current vs. Collector-emitter Voltage**

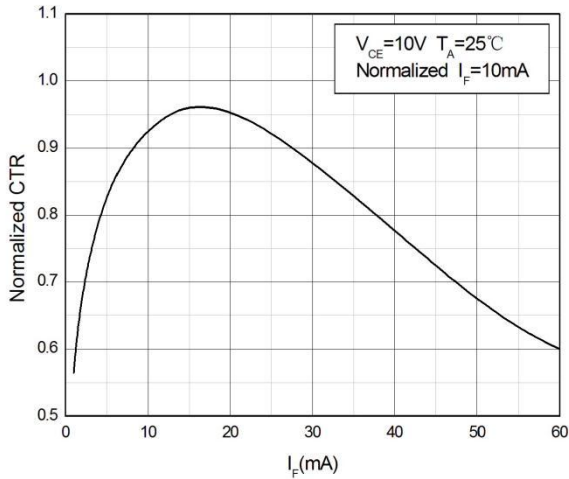


**Fig.6 Collector Current vs. Collector-emitter Voltage**

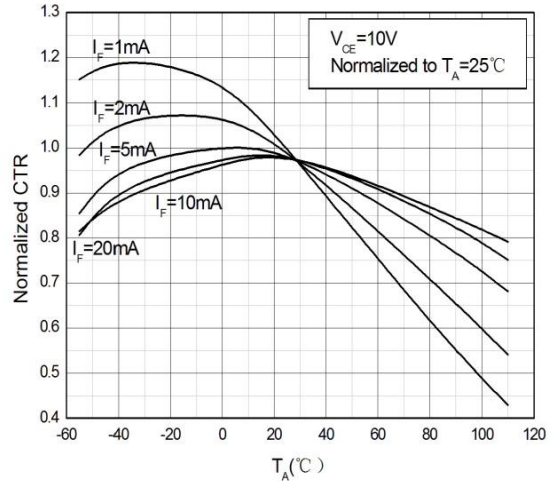


### CHARACTERISTIC CURVES

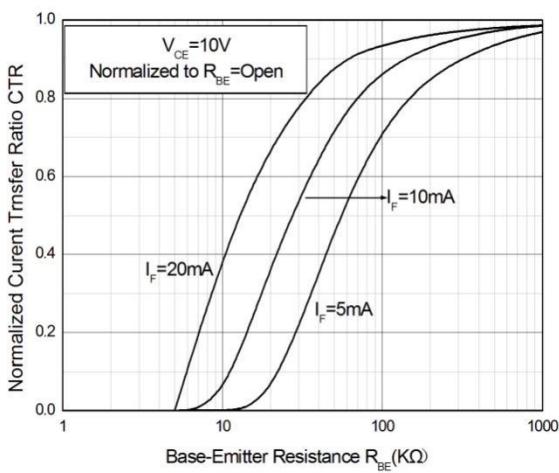
**Fig.7 Normalized Current Transfer Ratio vs. Forward Current**



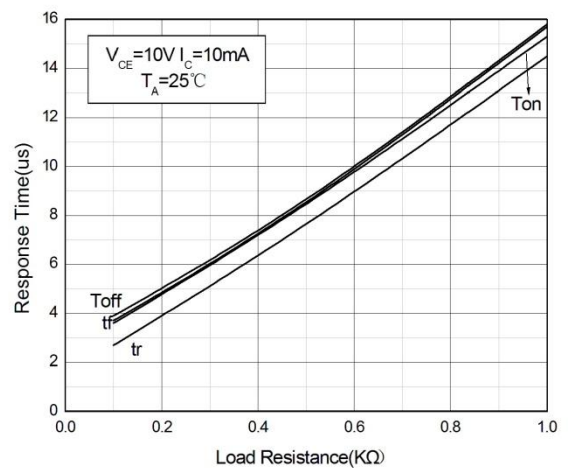
**Fig.8 Normalized Current Transfer Ratio vs. Ambient Temperature**



**Fig.9 Current Transfer Ratio(Unsaturated) vs Base-Emitter Resistance**

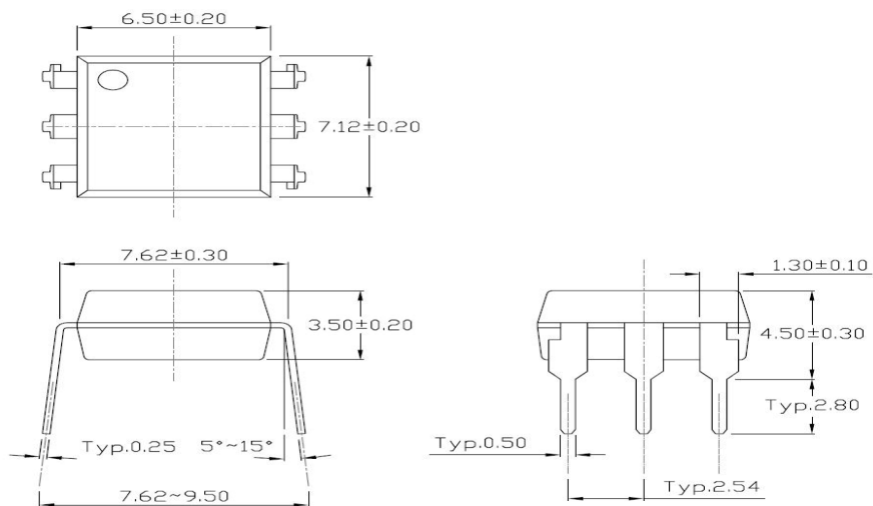


**Fig.10 Switching Time vs. Load Resistance**



**PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)**

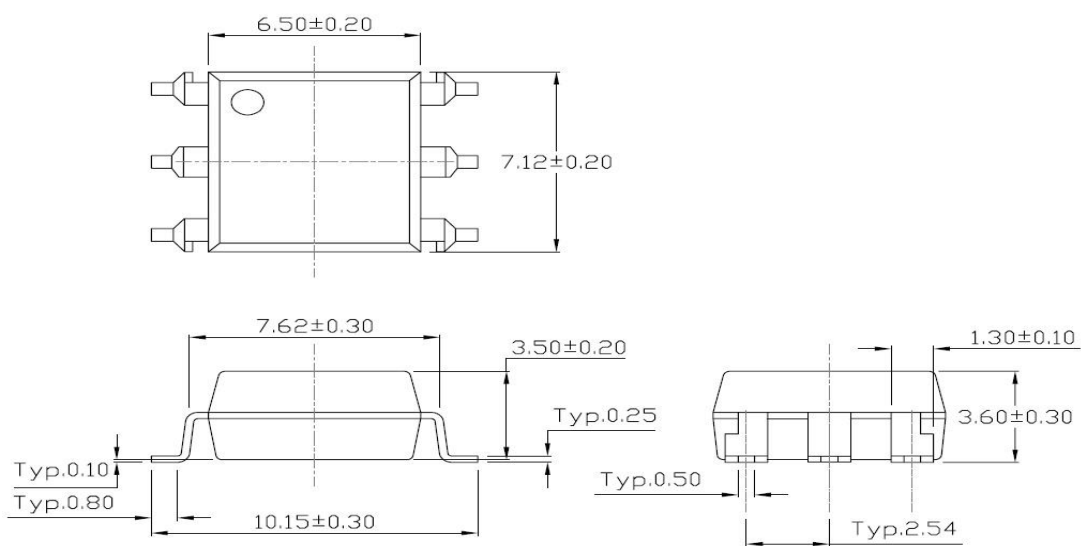
**Standard DIP – Through Hole (DIP Type)**



**Gullwing (400mil) Lead Forming – Through Hole (M Type)**

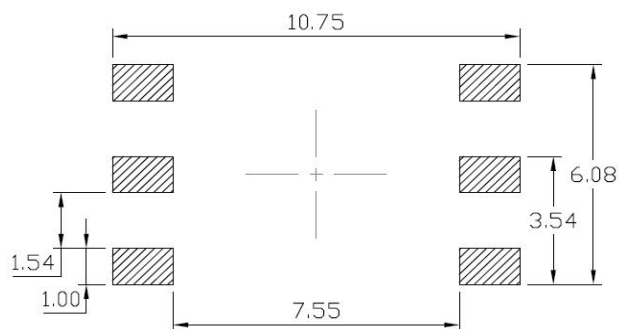
**PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)**

**Surface Mount (Low Profile) Lead Forming (SL Type)**



**Recommended Solder Mask (Dimensions in mm unless otherwise stated)**

**Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming**



## Marking

UMW  
4Nxx  
XXWW

- “XX” denotes YEAR;
- “WW” denotes WEEK

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